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(f) forming a dielectric film on the first electrode,

(g) forming a second electrode for the capacitor cell comprised of a second conductor film and a third conductor film on the dielectric film,

(h) forming a third insulating film over the capacitor cell,

(i) forming a mask with openings over the third insulating film,

(j) etching the second and third insulating films through the openings of the mask to make a first opening revealing the second electrode and a second opening revealing the first conductor film,

(k) forming a first conductor plug in the first opening and a second conductor plug in the second opening.

10. A method of manufacturing a semiconductor integrated circuit device according to claim 9, wherein the third insulating film is comprised of silicon oxide film.

11. A method of manufacturing a semiconductor integrated circuit device according to claim 10;

wherein the etching speed for the third conductor film is slower than the etching speed for the second conductor film by the etching method adopted in the step (j).

12. A method of manufacturing a semiconductor integrated circuit device according to claim 9;

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wherein the electric resistance of the third conductor film is smaller than the electric resistance of the second conductor film.

13. A method of manufacturing a semiconductor integrated circuit device according to claim 9, wherein:

the first conductor plug connects with the second electrode by an undersurface of the first conductor plug,
and the second conductor plug connects with the first conductor film by an undersurface of the second conductor plug.

14. A method of manufacturing a semiconductor integrated circuit device according to claim 9, wherein:

the dielectric film is comprised of tantalum-oxide film.

15. A method of manufacturing a semiconductor integrated circuit device according to claim 14, wherein:

the second conductor film is comprised of titanium nitride film.

16. A method of manufacturing a semiconductor integrated circuit device according to claim 14 wherein:

the third conductor film is comprised of tungsten film. --
